	Application No.	Applicant(s)	
′	40/700 200	LVONGETAL	
Notice of Allowability	10/790,366 Examiner	LYONS ET AL. Art Unit	
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	David S. Blum	2813	
The MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED i or other appropriate comm GHTS. This application is	n this application. If not include unication will be mailed in due	ed course. THIS
1. ☑ This communication is responsive to <u>1/17/06</u> .	•		
2. The allowed claim(s) is/are 1-4,8,9 and 21-28.			
3. ☐ Acknowledgment is made of a claim for foreign priority un a) ☐ All b) ☐ Some* c) ☐ None of the:		or (f).	
 Certified copies of the priority documents have 	• •		
2. Certified copies of the priority documents have			
Copies of the certified copies of the priority do	cuments have been receive	ed in this national stage applica	tion from the
International Bureau (PCT Rule 17.2(a)).	•		
* Certified copies not received:		•	
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		e a reply complying with the red	quirements
4. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which give			OTICE OF
5. CORRECTED DRAWINGS (as "replacement sheets") mus	t be submitted.		
(a) ☐ including changes required by the Notice of Draftspers		w (PTO-948) attached	
1) hereto or 2) to Paper No./Mail Date		,	
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	Amendment / Comment o	r in the Office action of	
Identifying indicia such as the application number (see 37 CFR 1, each sheet. Replacement sheet(s) should be labeled as such in the			back) of
6. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT			Note the
Attachment(s)			
1. Notice of References Cited (PTO-892)	5. Notice of I	nformal Patent Application (PT	O-152)
2. Notice of Draftperson's Patent Drawing Review (PTO-948)		Summary (PTO-413), ./Mail Date	
3. Information Disclosure Statements (PTO-1449 or PTO/SB/0	8), 7. Examiner's	Amendment/Comment	
Paper No./Mail Date 4. Examiner's Comment Regarding Requirement for Deposit	8. 🛭 Examiner's	Statement of Reasons for Allo	wance
of Biological Material	9. 🔲 Other		
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This action is in response to the amendment filed 1/17/06.

Allowable Subject Matter

- 1. Claims 1-4, 8-9, and 21-28 are allowed.
- The following is an examiner's statement of reasons for allowance: 2.

Claim 1 limits the fabrication of a shallow trench isolation to forming a polish stop layer on a substrate, forming a nitride containing layer over the polish stop layer and after forming a trench, removing the nitride containing layer and planarizing the trench (obviously filled) to the surface of the polish stop layer, oxidizing substantially all of the polish stop layer to convert the layer to a field oxide layer. This limitation, in combination with the other limitations of claim 1 is not taught or suggested by the prior art of record. Ajuria (US005837612A) removes the polish stop layer rather than oxidizing it. Tan (US006001706A) oxidizes a side of the polish stop layer and then removes the rest of the layer. Lyons (US005930645A) teaches a polysilicon layer as a replacement for a nitride containing polish stop layer, but does not teach a nitride layer over the polysilicon layer. Lyons also removes the polysilicon layer after oxidizing it.

Claims 2-4, 8-9, and 21-22 are allowed as being properly dependent upon allowed claim 1.

Claim 23 limits the fabrication of a shallow trench isolation to forming a polish stop layer of silicon carbide on a substrate, forming a nitride containing layer over the polish stop

Application/Control Number: 10/790,366

Art Unit: 2813

layer and after forming a trench, removing the nitride containing layer and planarizing the trench (obviously filled) to the surface of the polish stop layer. This limitation, in combination with the other limitations of claim 23 is not taught or suggested by the prior art of record. Ajuria (US005837612A), Tan (US006001706A), and Lyons (US005930645A) all teaches a polysilicon layer as a polish stop layer, but do not teach or suggest a silicon carbide polish stop layer. Olsen (US006555476B1) teaches a silicon carbide polish stop layer as an improvement to a nitride polish stop layer, but also teaches a nitride layer under the polish stop layer rather than over it. There is no teaching or suggestion for a nitride layer over the silicon carbide layer.

Claims 24-28 are allowed as being properly dependent upon allowed claim 23.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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Page 4

Any inquiry concerning this communication or earlier communications from the examiner should be directed to David S. Blum whose telephone number is (571)-272-1687) and e-mail address is David.blum@USPTO.gov.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead Jr., can be reached at (571)-272-1702. Our facsimile number all patent correspondence to be entered into an application is (571) 273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

David S. Blum

March 30, 2006